



80EBU02

Ultrafast Soft Recovery Diode

Features

- Ultrafast Recovery
- 175°C Operating Junction Temperature
- Screw Mounting Only
- Lead-Free Plating

Benefits

- Reduced RFI and EMI
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

$t_{rr} = 35\text{ns}$
$I_{F(AV)} = 80\text{Amp}$
$V_R = 200\text{V}$

Description/ Applications

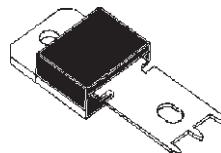
These diodes are optimized to reduce losses and EMI/ RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

Absolute Maximum Ratings

Parameters	Max	Units
V_R Cathode to Anode Voltage	200	V
$I_{F(AV)}$ Continuous Forward Current, $T_C = 112^\circ\text{C}$	80	A
I_{FSM} Single Pulse Forward Current, $T_C = 25^\circ\text{C}$	800	
I_{FRM} ① Maximum Repetitive Forward Current	160	
T_J, T_{STG} Operating Junction and Storage Temperatures	- 55 to 175	°C

① Square Wave, 20kHz

Case Styles



PowIRtab

80EBU02

Bulletin PD-20740 rev. B 02/06

 International
 Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
V_{BR} , V_r	Breakdown Voltage, Blocking Voltage	200	-	-	V	$I_R = 50\mu\text{A}$
V_F	Forward Voltage	-	0.98	1.13	V	$I_F = 80\text{A}$
		-	0.79	0.92	V	$I_F = 80\text{A}$, $T_J = 175^\circ\text{C}$
I_R	Reverse Leakage Current	-	-	50	μA	$V_R = V_R$ Rated
		-	-	2	mA	$T_J = 150^\circ\text{C}$, $V_R = V_R$ Rated
C_T	Junction Capacitance	-	89	-	pF	$V_R = 200\text{V}$
L_S	Series Inductance	-	3.5	-	nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Units	Test Conditions
t_{rr}	Reverse Recovery Time	-	-	35	ns	$I_F = 1.0\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$, $V_R = 30\text{V}$
		-	32	-		$T_J = 25^\circ\text{C}$
		-	52	-		$T_J = 125^\circ\text{C}$
I_{RRM}	Peak Recovery Current	-	4.4	-	A	$T_J = 25^\circ\text{C}$
		-	8.8	-		$T_J = 125^\circ\text{C}$
Q_{rr}	Reverse Recovery Charge	-	70	-	nC	$T_J = 25^\circ\text{C}$
		-	240	-		$T_J = 125^\circ\text{C}$

Thermal - Mechanical Characteristics

Parameters		Min	Typ	Max	Units
R_{thJC}	Thermal Resistance, Junction to Case		0.2	0.70	K/W
R_{thCS} ②	Thermal Resistance, Case to Heatsink				
Wt	Weight		0.18	5.02	g
					(oz)
T	Mounting Torque	1.2		2.4	$\text{N} * \text{m}$
		10		20	lbf.in

② Mounting Surface, Flat, Smooth and Greased

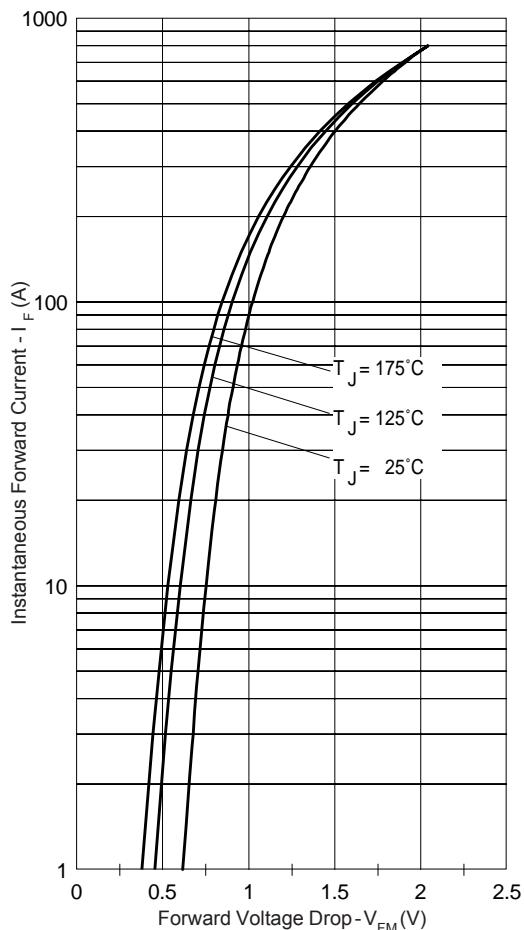


Fig.1 - Typical Forward Voltage Drop Characteristics

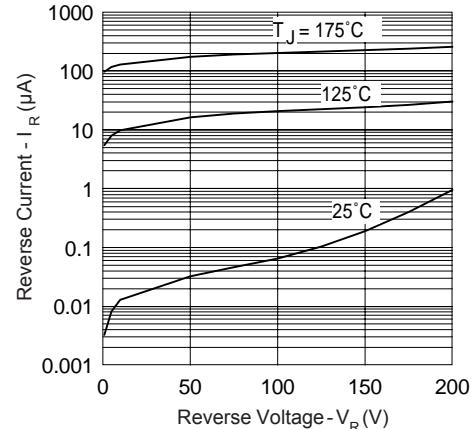


Fig.2 - Typical Values Of Reverse Current Vs. Reverse Voltage

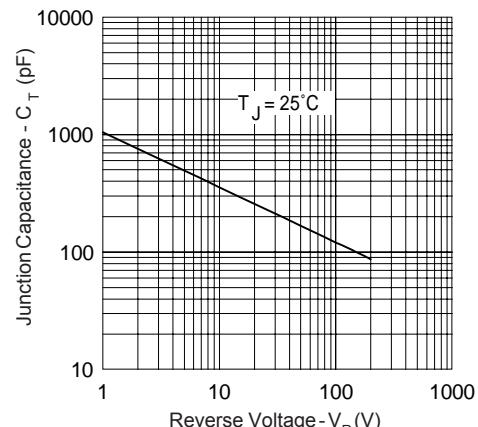


Fig.3 - Typical Junction Capacitance Vs. Reverse Voltage

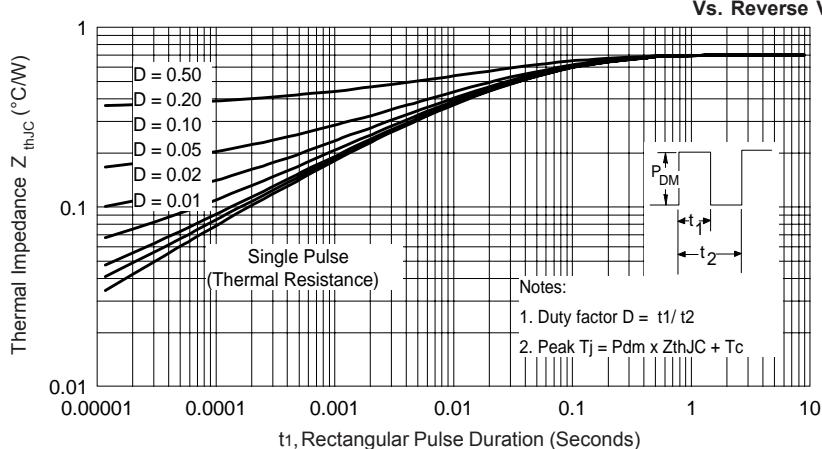


Fig.4 - Max. Thermal Impedance Z_thJC Characteristics

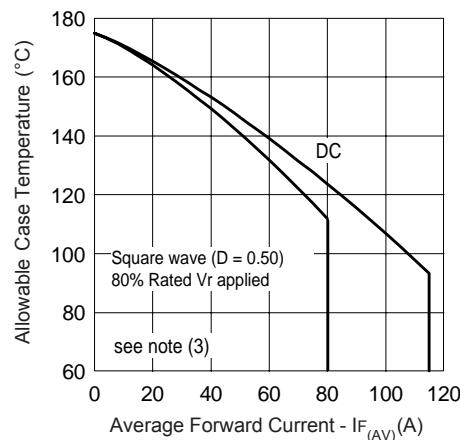


Fig. 5 - Max. Allowable Case Temperature Vs. Average Forward Current

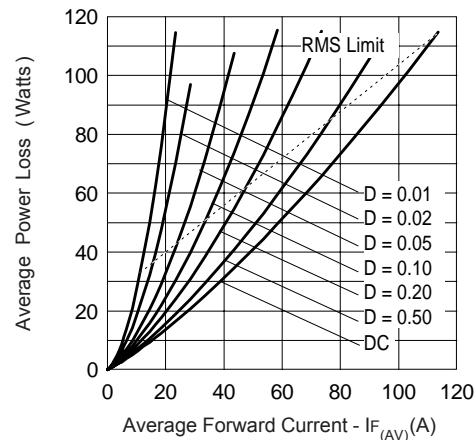
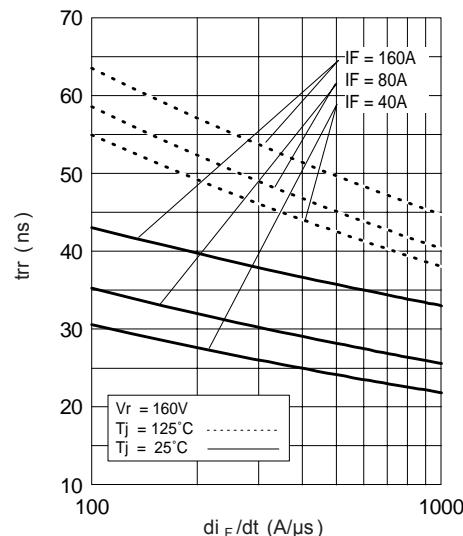
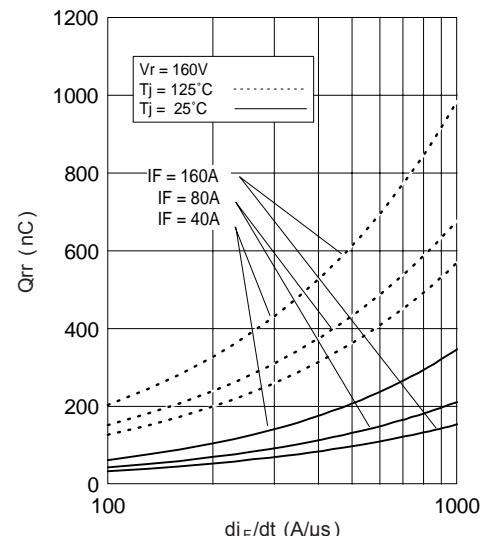


Fig. 6 - Forward Power Loss Characteristics

Fig. 7 - Typical Reverse Recovery time vs. di_F/dt Fig. 8 - Typical Stored Charge vs. di_F/dt

(3) Formula used: $T_c = T_j - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 $P_d = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$ (see Fig. 6);
 $P_{d_{REV}} = \text{Inverse Power Loss} = V_{R1} \times I_R (1 - D)$; $I_R @ V_{R1} = 80\% \text{ rated } V_R$

Reverse Recovery Circuit

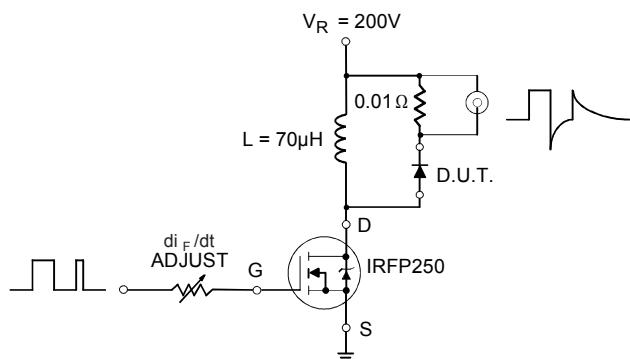


Fig. 9- Reverse Recovery Parameter Test Circuit

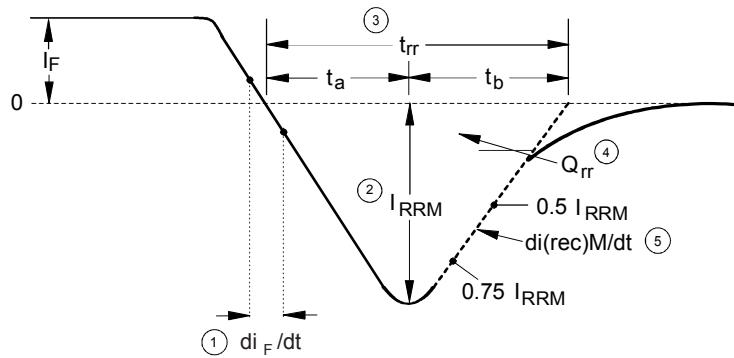
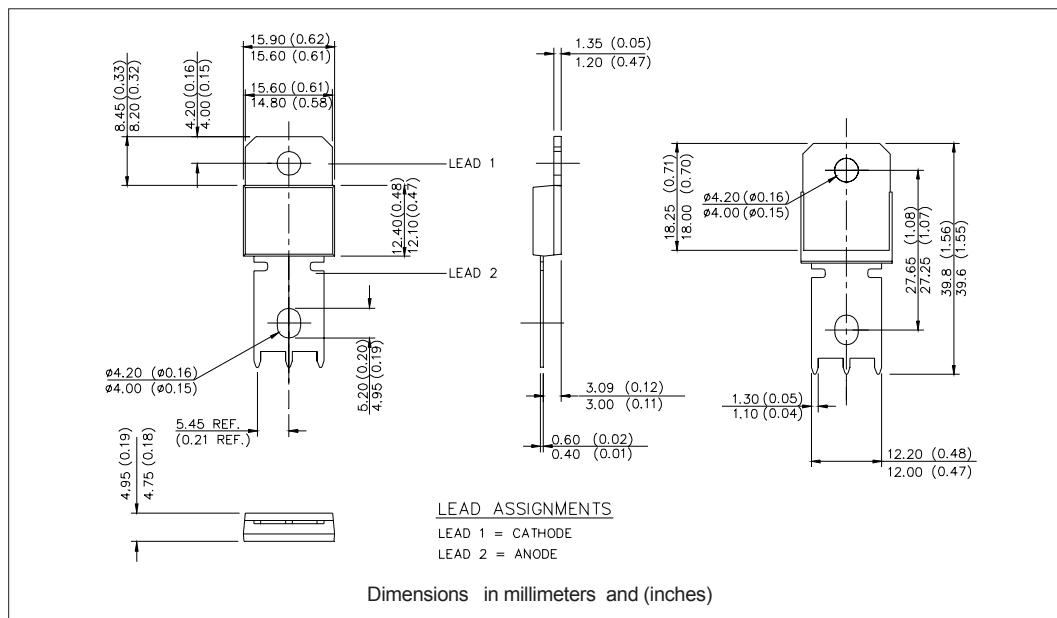


Fig. 10 - Reverse Recovery Waveform and Definitions

Outline Table



Ordering Information Table

Device Code		80	E	B	U	02
		1	2	3	4	5
1	-	Current Rating			(80 = 80A)	
2	-	Single Diode				
3	-	PowIRtab			(Ultrafast/ Hyperfast only)	
4	-	Ultrafast Recovery				
5	-	Voltage Rating			(02 = 200V)	

Data and specifications subject to change without notice.
 This product has been designed and qualified for Industrial Level and Lead-Free.
 Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
 TAC Fax: (310) 252-7309
 02/06



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